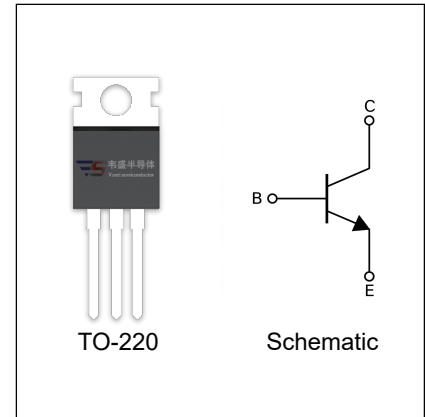


MJE3055 TRANSISTOR (NPN)

FEATURES

- General Purpose and Switching Applications



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	10	A
P_C	Collector Power Dissipation	2	W
T_j, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=200mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=70V, I_E=0$			1	mA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			5	mA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=4V, I_C=4A$	20		100	
	$h_{FE(2)}^*$	$V_{CE}=4V, I_C=10A$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=4A, I_B=0.4A$			1.1	V
	$V_{CE(sat)}^*$	$I_C=10A, I_B=3.3A$			8	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=4V, I_C=4A$			1.8	V
Transition frequency	f_T	$V_{CE}=10V, I_C=0.5A$	2			MHz

Note:*Pulse test: $t_p \leq 300\mu S$, $\delta \leq 0.02$.

Static Characteristic
